

# Seunggeun Lee

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Demonstration of GaN-based vertical-cavity surface-emitting lasers with buried tunnel junction contacts. Optics Express, 2019, 27, 31621.	1.7	33
2	Continuous-wave operation of <i>m</i> -plane GaN-based vertical-cavity surface-emitting lasers with a tunnel junction intracavity contact. Applied Physics Letters, 2018, 112, .	1.5	44
3	GaN-based vertical-cavity surface-emitting lasers with tunnel junction contacts grown by metal-organic chemical vapor deposition. Applied Physics Express, 2018, 11, 062703.	1.1	51
4	Smooth and selective photo-electrochemical etching of heavily doped GaN:Si using a mode-locked 355 nm microchip laser. Applied Physics Express, 2017, 10, 011001.	1.1	13
5	Nonpolar GaN-based vertical-cavity surface-emitting lasers. , 2017, , .		1
6	Dynamic characteristics of 410-nm semipolar (202 $\hat{A}$ -1 $\hat{A}$ ) III-nitride laser diodes with a modulation bandwidth of over 5 GHz. Applied Physics Letters, 2016, 109, .	1.5	27
7	Nonpolar III-nitride vertical-cavity surface-emitting laser with a photoelectrochemically etched air-gap aperture. Applied Physics Letters, 2016, 108, 031111.	1.5	39
8	High speed performance of III-nitride laser diode grown on (2021) semipolar plane for visible light communication. , 2016, , .		4
9	Nonpolar III-nitride vertical-cavity surface-emitting lasers incorporating an ion implanted aperture. Applied Physics Letters, 2015, 107, .	1.5	85